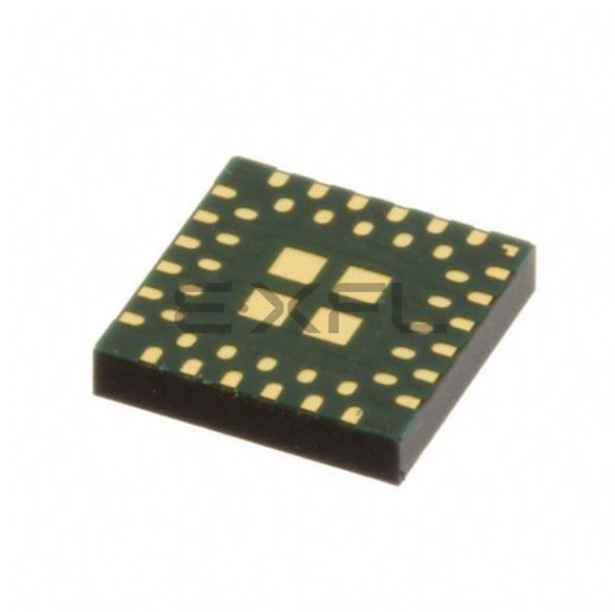

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	DMA, WDT
Number of I/O	20
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 5x16b, 4x24b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-VFLGA Exposed Pad
Supplier Device Package	44-MAPLGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkm14z128chh5r

4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.6	V
V_{DIO}	Digital input voltage (except $\overline{\text{RESET}}$, EXTAL, and XTAL)	–0.3	V_{DD} + 0.3	V
$V_{DTamper}$	Tamper input voltage	–0.3	V_{BAT} + 0.3	V
V_{AIO}	Analog[1], $\overline{\text{RESET}}$, EXTAL, and XTAL input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V
V_{BAT}	RTC battery supply voltage	–0.3	3.6	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5 General

5.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

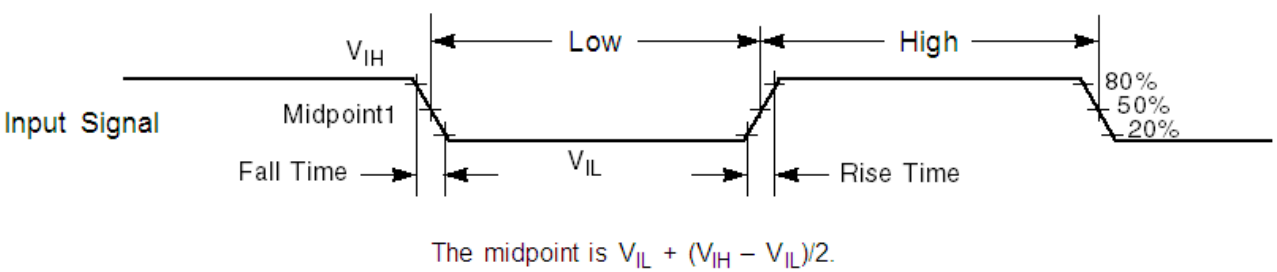

Figure 1. Input signal measurement reference

5.2 Nonswitching electrical specifications

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes

I_{DD_VBAT}	Average current when VDD is OFF and LFSR and Tamper clocks set to 2 Hz.
	• @ 3.0 V
	  • 25 °C
	  • -40 °C
	  • 105 °C
		—	1.3 [7]	3
				2.5
				16
					µA
					µA
					µA
						8, 9

1. See AFE specification for IDDA.
2. 50 MHz core and system clock, 25 MHz bus clock, and 25 MHz flash clock. MCG configured for FBE mode. All peripheral clocks disabled.
3. Should be reduced by 500 µA.
4. 2 MHz core, system, bus clock, and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing while (1) loop from flash.
5. 2 MHz core, system and bus clock, and 1MHz flash clock. MCG configured for BLPE mode. All peripheral clocks enabled but peripherals are not in active operation. Code executing while (1) loop from flash.
6. 2 MHz core, system and bus clock, and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. No flash accesses; some activity on DMA & RAM assumed.
7. Current consumption will vary with number of CPU accesses done and is dependent on the frequency of the accesses and frequency of bus clock. Number of CPU accesses should be optimized to get optimal current value.
8. Includes 32 kHz oscillator current and RTC operation.
9. An external power switch for VBAT should be present on board to have better battery life and keep VBAT pin powered in all conditions. There is no internal power switch in RTC.

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	14	dBµV	1, 2
V_{RE2}	Radiated emissions voltage, band 2	50–150	16	dBµV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	12	dBµV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	5	dBµV	
V_{RE_IEC}	IEC level	0.15–1000	M	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.
2. V_{DD} = 3.3 V, T_A = 25 °C, f_{OSC} = 10 MHz (crystal), f_{SYS} = 50 MHz, f_{BUS} = 25 MHz
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

5.3.2 General switching specifications

These general purpose specifications apply to all signals configured for GPIO, UART, and I^2C signals.

Table 10. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Asynchronous path	16	—	ns	2
	External reset pulse width (digital glitch filter disabled)	100	—	ns	2
	Port rise and fall time—Low (All pins) and high drive (only PTC2) strength				3
	• Slew disabled				
	• $1.71 \le V_{DD} \le 2.7$ V	—	8	ns	
	• $2.7 \le V_{DD} \le 3.6$ V	—	5	ns	
	• Slew enabled				
	• $1.71 \le V_{DD} \le 2.7$ V	—	27	ns	
	• $2.7 \le V_{DD} \le 3.6$ V	—	16	ns	

1. The greater synchronous and asynchronous timing must be met.
2. This is the shortest pulse that is guaranteed to be recognized.
3. Only PTC2 has high drive capability and load is 75 pF, other pins load (low drive) is 25 pF.

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 11. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	–40	105	°C
T_A	Ambient temperature	–40	85	°C

5.4.2 Thermal attributes

Board type	Symbol	Description	100 LQFP	44 LGA	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	63	95	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	50	50	°C/W	1
Single-layer (1s)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	53	79	°C/W	1
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	44	45	°C/W	1
—	$R_{\theta JB}$	Thermal resistance, junction to board	36	35	°C/W	2
—	$R_{\theta JC}$	Thermal resistance, junction to case	18	28	°C/W	3
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	3	4	°C/W	4

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)*.
2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*.
3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
4. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.

6 Peripheral operating requirements and behaviors

Case 2: Clock is going Out and Data is coming In (XBAR ports timed with respect to generated clock defined at the XBAR out ports)

Table 15. AFE switching characteristics (2.7V-3.6V)

Symbol	Description	Value	Unit	Notes
AFE CLK	Frequency of operation	6.2	MHz	
Inputs, tSUI	Data setup time	36	ns	
inputs,tHI	Data hold time	0	ns	

AFE switching characteristics at (1.7 V-3.6 V)

Case1: Clock is coming In and Data is also coming In (XBAR ports timed with respect to AFE clock defined at pad ptb[7] and pte[3])

Table 16. AFE switching characteristics (1.7 V-3.6 V)

Symbol	Description	Value	Unit	Notes
AFE CLK	Frequency of operation	10	MHz	
Inputs, tSUI	Data setup time	5.1	ns	
inputs,tHI	Data hold time	0	ns	

Case 2: Clock is going Out and Data is coming In (XBAR ports timed with respect to generated clock defined at XBAR out ports)

Table 17. AFE switching characteristics (1.7 V-3.6 V)

Symbol	Description	Value	Unit	Notes
AFE CLK	Frequency of operation	6.2	MHz	
Inputs, tSUI	Data setup time	54	ns	
inputs,tHI	Data hold time	0	ns	

6.2 Clock modules

6.2.1 MCG specifications

Table 18. MCG specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal VDD and 25 °C	—	32.768	—	kHz	

Table continues on the next page...

Table 18. MCG specifications (continued)

Symbol	Description		Min.	Typ.	Max.	Unit	Notes
Δf_{ints_t}	Total deviation of internal reference frequency (slow clock) over voltage and temperature		—	± 4	± 15	%	
f_{ints_t}	Internal reference frequency (slow clock) — user trimmed		31.25	—	33.4234	kHz	
$\Delta_{fdco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM		—	± 0.3	± 0.6	$\%f_{dco}$	1
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over voltage and temperature		—			$\%f_{dco}$	1
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over fixed voltage and temperature range of 0–70°C		—			$\%f_{dco}$	1
f_{intf_ft}	Internal reference frequency (fast clock) — factory trimmed at nominal VDD and 25°C				4	MHz	
Δf_{intf_t}	Total deviation of internal reference frequency (fast clock) over voltage and temperature		—	± 10	± 15	%	
f_{intf_t}	Internal reference frequency (fast clock) — user trimmed at nominal VDD and 25 °C		3	—	5	MHz	
f_{loc_low}	Loss of external clock minimum frequency — RANGE = 00		(3/5) x f_{ints_t}	—	—	kHz	
f_{loc_high}	Loss of external clock minimum frequency — RANGE = 01, 10, or 11		(16/5) x f_{ints_t}	—	—	kHz	
FLL							
f_{dco}	DCO output frequency range	Low-range (DRS=00) 640 × f_{ints_t}	20	20.97	22	MHz	2, 3
		Mid-range (DRS=01) 1280 × f_{ints_t}	40	41.94	45	MHz	
		Mid-high range (DRS=10) 1920 × f_{ints_t}	60	62.91	67	MHz	
		High-range (DRS=11) 2560 × f_{ints_t}	80	83.89	90	MHz	
$f_{dco\_t\_DMX32}$	DCO output frequency	Low-range (DRS=00) 732 × f_{ints_t}	—	23.99	—	MHz	4, 5, 6
		Mid-range (DRS=01) 1464 × f_{ints_t}	—	47.97	—	MHz	
		Mid-high range (DRS=10) 2197 × f_{ints_t}	—	71.99	—	MHz	
		High-range (DRS=11) 2929 × f_{ints_t}	—	95.98	—	MHz	
J_{cyc_fll}	FLL period jitter		—	70	140	ps	7
$t_{fll\_acquire}$	FLL target frequency acquisition time		—	—	1	ms	8
PLL							

Table continues on the next page...

Table 18. MCG specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{vco}	VCO operating frequency	11.71875	12.288	14.6484375	MHz	
I_{pll}	PLL operating current • IO 3.3 V current • Max core voltage current	—	300 100	—	µA	9
f_{pll_ref}	PLL reference frequency range	31.25	32.768	39.0625	kHz	
J_{cyc_pll}	PLL period jitter (RMS) • f_{vco} = 12 MHz			700	ps	10
D_{lock}	Lock entry frequency tolerance	± 1.49	—	± 2.98	%	11
D_{unl}	Lock exit frequency tolerance	± 4.47	—	± 5.97	%	
t_{pll_lock}	Lock detector detection time	—	—	$150 \times 10^{-6} + 1075(1/f_{pll\_ref})$	s	12

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=0.
3. Chip max freq is 50 MHz, so Mid-range with DRS = 10 and High-range of DCO cannot be used and should not be configured.
4. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=1.
5. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
6. Chip max freq is 50 MHz, so Mid-range with DRS = 10 and High-range of DCO cannot be used and should not be configured.
7. This specification is based on standard deviation (RMS) of period or frequency.
8. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
9. Excludes any oscillator currents that are also consuming power while PLL is in operation.
10. This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
11. Will be updated later
12. This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

6.2.2 Oscillator electrical specifications

6.2.2.1 Oscillator DC electrical specifications

Table 19. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	

Table continues on the next page...

Table 22. 32 kHz oscillator frequency specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{start}	Crystal start-up time	—	1000	—	ms	1
$v_{ec\_extal32}$	Externally provided input clock amplitude	700	—	V_{BAT}	mV	2 , 3

1. Proper PC board layout procedures must be followed to achieve specifications.
2. This specification is for an externally supplied clock driven to EXTAL32 and does not apply to any other clock input. The oscillator remains enabled and XTAL32 must be left unconnected.
3. The parameter specified is a peak-to-peak value and V_{IH} and V_{IL} specifications do not apply. The voltage of the applied clock must be within the range of V_{SS} to V_{BAT}.

NOTE

The 32 kHz oscillator works in low power mode by default and cannot be moved into high power/gain mode.

6.3 Memories and memory interfaces

6.3.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

6.3.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 23. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	µs	
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversall}$	Erase All high-voltage time	—	52	452	ms	1

1. Maximum time based on expectations at cycling end-of-life.

6.3.1.2 Flash timing specifications — commands

Table 24. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	µs	1
t_{pgmchk}	Program Check execution time	—	—	45	µs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	µs	1

Table continues on the next page...

6.4.1.1 16-bit ADC operating conditions

Table 27. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V_{DD} (V_{DD} – V_{DDA})	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} (V_{SS} – V_{SSA})	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	
V_{ADIN}	Input voltage		V_{REFL}	—	V_{REFH}	V	
C_{ADIN}	Input capacitance	• 16-bit mode • 8-bit / 10-bit / 12-bit modes	— —	8 4	10 5	pF	
R_{ADIN}	Input series resistance		—	2	5	kΩ	
R_{AS}	Analog source resistance (external)	12-bit modes f_{ADCK} < 4 MHz	—	—	5	kΩ	3
f_{ADCK}	ADC conversion clock frequency	≤ 12-bit mode	1.0	—	18.0	MHz	4
f_{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C_{rate}	ADC conversion rate	≤ 12-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	5
C_{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	Ksps	5

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
4. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

Table 29. Comparator and 6-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	µs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	µA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD}–0.6 V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to CMP_DACCR[DACEN], CMP_DACCR[VRSEL], CMP_DACCR[VOSEL], CMP_MUXCR[PSEL], and CMP_MUXCR[MSEL]) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}$/64

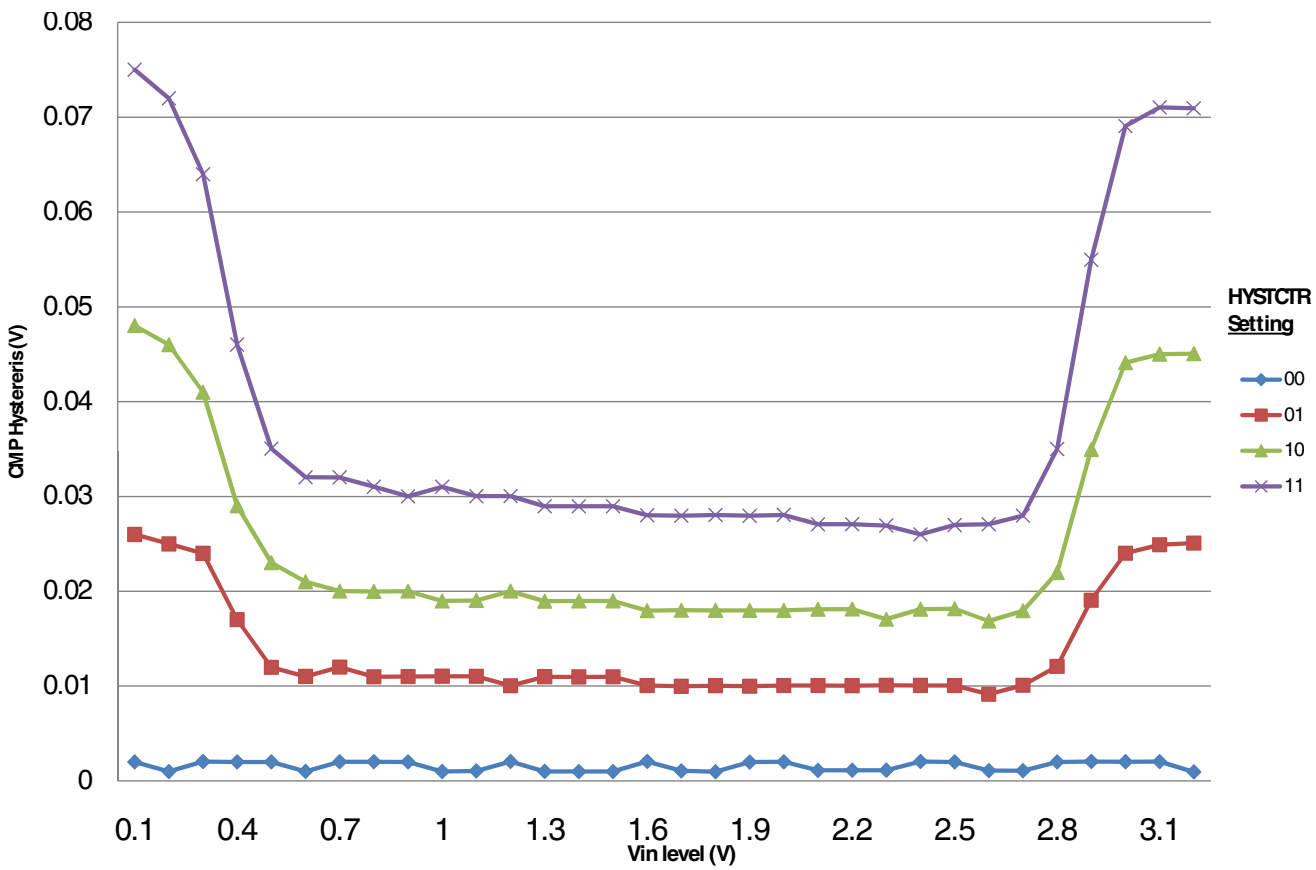

Figure 4. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 0)

Table 31. VREF full-range operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
VREFH	Voltage reference output — user trim	1.178	—	1.202	V	
VREFL	Voltage reference output	0.38	0.4	0.42	V	
V_{step}	Voltage reference trim step	—	0.5	—	mV	
V_{tdrift}	Temperature drift (Vmax - Vmin across the full temperature range)	—	5	—	mV	1
Ac	Aging coefficient	—	—	400	uV/yr	
I_{bg}	Bandgap only current	—	—	80	µA	2
I_{lp}	Low-power buffer current	—	—	0.19	µA	2
I_{hp}	High-power buffer current	—	—	0.5	mA	2
I_{LOAD}	VREF buffer current	—	—	1	mA	3
ΔV_{LOAD}	Load regulation • current = + 1.0 mA • current = - 1.0 mA	—	 2 5	—	mV	2, 4
T_{stup}	Buffer startup time	—	—	20	ms	
V_{vdrift}	Voltage drift (Vmax -Vmin across the full voltage range)	—	0.5	—	mV	2

1. For temp range -40 °C to 105 °C, this value is 15 mV
2. See the chip's Reference Manual for the appropriate settings of VREF Status and Control register.
3. See the chip's Reference Manual for the appropriate settings of SIM Miscellaneous Control Register.
4. Load regulation voltage is the difference between VREFH voltage with no load vs. voltage with defined load.

Table 32. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_A	Temperature	0	50	°C	

Table 33. VREF limited-range operating behaviours

Symbol	Description	Min.	Max.	Unit	Notes
VREFH	Voltage reference output with factory trim	1.173	1.225	V	
VREFL	Voltage reference output	0.38	0.42	V	

6.4.4 AFE electrical specifications

6.4.4.2 ΣΔ ADC Standalone specifications

Table 35. ΣΔ ADC standalone specifications

Symbol	Description	Conditions	Min	Typ[1]	Max	Unit	Notes
f_{Nyq}	Input bandwidth	Normal Mode	1.5	1.5	1.5	kHz	
		Low-Power Mode	1.5	1.5	1.5		
V_{CM}	Input Common Mode Reference		0		0.8	V	
VIN_{diff}	Input range	Differential		+/- 500		mV	
		Single Ended		+/- 250		mV	
SNR	Signal to Noise Ratio	Normal Mode • f_{IN}=50Hz; common mode=0V, V_{pp}= 500mV (differential ended) • f_{IN}=50Hz; common mode=0V, V_{pp}= 500mV (full range se.) Low-Power Mode • f_{IN}=50Hz; common mode=0V, V_{pp}=500mV (diff.) • f_{IN}=50Hz; common mode=0V, V_{pp}=500mV (full range se.)	88 76	90 78		dB	
$\Delta Gain_{Temp}$	Gain Temperate Drift - Gain error caused by temperature drifts [2]	• Gain bypassed Vpp = 500 mV (differential) • PGA bypassed Vpp = 500 mV (differential), VCM = 0 V			55	ppm/°C	
$\Delta Offset_{Temp}$	Offset Temperate Drift - Offset error caused by temperature drifts [3]	• Gain bypassed Vpp = 500 mV (differential), VCM = 0 V			30	ppm/°C	
SINAD	Signal-to-Noise + Distortion Ratio	Normal Mode • f_{IN}=50Hz; common mode=0V, V_{pp}= 500mV (diff.) • f_{IN}=50Hz; common mode=0V, V_{pp}= 500mV (full range se.) Low-Power Mode • f_{IN}=50Hz; common mode=0V, V_{pp}=500mV (diff.) • f_{IN}=50Hz; common mode=0V, V_{pp}=500mV (full range se.)		80 74		dB	
CMMR	Common Mode Rejection Ratio	• f_{IN}=50Hz; common mode=0V, V_{id}=100 mV		90		dB	
$PSRR_{AC}$	AC Power Supply Rejection Ratio	Gain=01, VCC = 3V ± 100mV, f_{IN} = 50 Hz		60		dB	
XT	Crosstalk	Gain=01, V_{id} = 500 mV, f_{IN} = 50 Hz			-100	dB	
f_{MCLK}	Modulator Clock Frequency Range	Normal Mode	0.03		6.5	MHz	
		Low-Power Mode	0.03		1.6		
I_{DDA_ADC}	Current Consumption by ADC (each channel)	Normal Mode (f_{MCLK} = 6.144 MHz, OSR= 2048)			1.4	mA	
		Low-Power Mode (f_{MCLK} = 0.768MHz, OSR= 256)			0.5		

1. Typical values assume VDDA = 3.0 V, Temp = 25°C, f_{MCLK} = 6.144 MHz, OSR = 2048 for Normal mode and f_{MCLK} = 768 kHz, OSR = 256 for Low-Power Mode unless otherwise stated. Typical values are for reference only and are not tested in production.
2. Represent combined gain temperature drift of the SD ADC, and Internal 1.2 VREF blocks.
3. Represent combined offset temperature drift of the SD ADC, and Internal 1.2 VREF blocks; Defined by shorting both differential inputs to ground.

6.4.4.3 External modulator interface

The external modulator interface on this device comprises of a Clock signal and 1-bit data signal. Depending on the modulator device being used the interface works as follows:

- Clock supplied to external modulator which drives data on rising edge and the KM device captures it on falling edge or next rising edge.
- Clock and data are supplied by external modulator and KM device can sample it on falling edge or next rising edge.

Depending on control bit in AFE, the sampling edge is changed.

6.5 Timers

See General switching specifications.

6.6 Communication interfaces

6.6.1 I2C switching specifications

See General switching specifications.

6.6.2 UART switching specifications

See General switching specifications.

6.6.3 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following table provides some reference values to be met on SoC.

Table 36. SPI switching characteristics at 2.7 V (2.7 - 3.6)

Description	Min.	Max.	Unit	Notes
Frequency of operation (F_{sys})	—	50	MHz	1
SCK frequency • Master • Slave	2	12.5 12.5	MHz Mhz	3
SCK Duty Cycle	50%	—	—	
Data Setup Time (inputs, tSUI) • Master • Slave	25 3		ns	
Input Data Hold Time (inputs, tHI) • Master • Slave	0 1		ns	
Data hold time (outputs, tHO) • Master • Slave	0 0		ns	
Data Valid Out Time (after SCK edge, tDVO) • Master • Slave	13 28		ns	
Rise time input • Master • Slave	1 1		ns	
Fall time input • Master • Slave	1 1		ns	
Rise time output • Master • Slave	8.9 8.9		ns	
Fall time output • Master • Slave	7.8 7.8		ns	

1. SPI modules will work on core clock.
2. F_{sys}/(Max Divider Value from registers)
3. F_{SYS}/2 in Master mode and F_{SYS}/4 in Slave mode. F_{SYS}/4 in Master as well as Slave Modes, where F_{SYS}=50Mhz

NOTE

The values assumed for input transition and output load are:
Input transition = 1 ns Output load = 50 pF

Table 37. SPI switching characteristics at 1.7 V (1.7 - 3.6)

Description	Min.	Max.	Unit	Notes
Frequency of operation (F_{sys})	—	50	MHz	

Table continues on the next page...

6.7.1 LCD electrical characteristics

Table 40. LCD electricals

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{Frame}	LCD frame frequency	28	30	58	Hz	
C_{LCD}	LCD charge pump capacitance — nominal value	—	100	—	nF	1
C_{BYLCD}	LCD bypass capacitance — nominal value	—	100	—	nF	1
C_{Glass}	LCD glass capacitance	—	2000	8000	pF	2
V_{IREG}	V_{IREG}					3
	• HREFSEL=0, RVTRIM=1111	—	1.11	—	V	
	• HREFSEL=0, RVTRIM=1000	—	1.01	—	V	
	• HREFSEL=0, RVTRIM=0000	—	0.91	—	V	
Δ_{RTRIM}	V_{IREG} TRIM resolution	—	—	3.0	% V_{IREG}	
I_{VIREG}	V_{IREG} current adder — RVEN = 1	—	1	—	µA	4
I_{RBIAS}	RBIAS current adder	—	15	—	µA	
	• LADJ = 10 or 11 — High load (LCD glass capacitance ≤ 8000 pF)	—	3	—	µA	
	• LADJ = 00 or 01 — Low load (LCD glass capacitance ≤ 2000 pF)					
VLL2	VLL2 voltage					
	• HREFSEL = 0	2.0 – 5%	2.0	—	V	
VLL3	VLL3 voltage	3.0 – 5%	3.0	—	V	

1. The actual value used could vary with tolerance.
2. For highest glass capacitance values, LCD_GCR[LADJ] should be configured as specified in the LCD Controller chapter within the device's reference manual.
3. V_{IREG} maximum should never be externally driven to any level other than V_{DD} - 0.15 V.
4. 2000 pF load LCD, 32 Hz frame frequency.

NOTE

KM family devices have a 1/3 bias controller that works with a 1/3 bias LCD glass. To avoid ghosting, the LCD OFF threshold should be greater than VLL1 level. If the LCD glass has an OFF threshold less than VLL1 level, use the internal VREG mode and generate VLL1 internally using RVTRIM option. This can reduce VLL1 level to allow for a lower OFF threshold LCD glass.

7 Dimensions

100 QFP	64 QFP	44 LGA	DEFAULT	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
93	57	—	Disabled	LCD21	PTI2						
94	58	—	Disabled	LCD22	PTI3						
95	59	—	VSS	VSS							
96	60	—	VLL3	VLL3							
97	61	—	VLL2	VLL2							
98	62	—	VLL1	VLL1							
99	63	—	VCAP2	VCAP2							
100	64	—	VCAP1	VCAP1							

8.2 KM Family Pinouts

8.2.1 100-pin LQFP

The following figure represents the KM 100 LQFP pinouts:

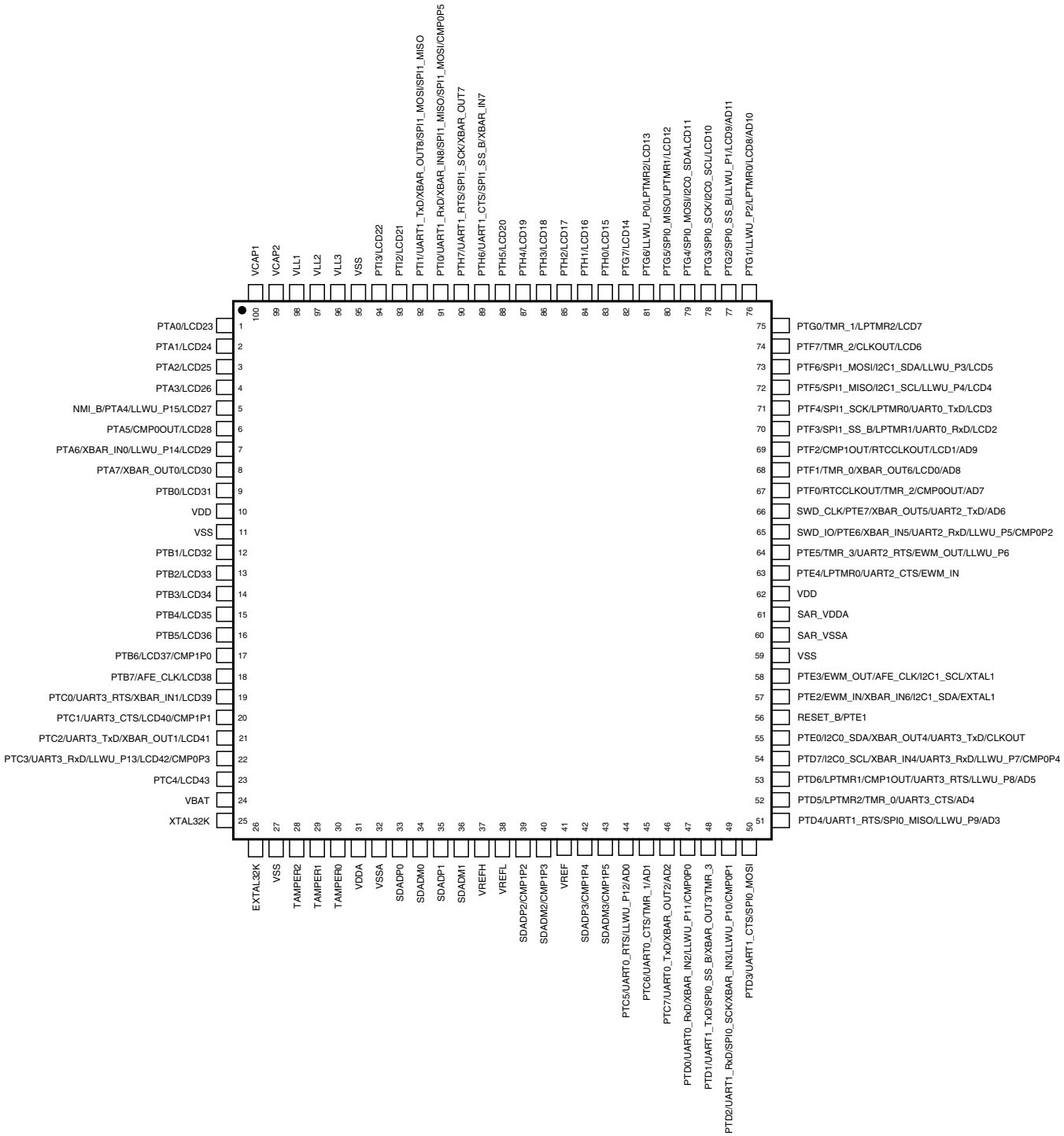

Figure 6. 100-pin LQFP Pinout Diagram

8.2.2 64-pin LQFP

The following figure represents 64-pin LQFP pinouts:

Table 41. Revision History

Rev. No.	Date	Substantial Changes
Rev1	10/2012	Initial release
Rev2	01/2013	Updated part numbers Updated Table: Power mode transition operating behaviors Updated Table: Power consumption operating behaviors. Included readings for temperature - 40 °C, 25 °C, and 85 °C Updated AFE Modulator clock maximum value in table “Device clock specifications” Updated Table: General switching specifications Updated Table: Thermal operating requirements Updated Table: SWD switching specifications Added Table: AFE (Analog Frontend) Switching characteristics Updated Table: Oscillator DC electrical specifications Updated Table: ΣΔ ADC + PGA specifications Under section SPI switching specification, • Table SPI timing renamed to SPI switching characteristics at 2.7 V (2.7 - 3.6) • Modified row: “Data Hold Time (inputs, tHI)” to “Input Data Hold Time (inputs, tHI)” • Modified row: “Data valid time (after SCK edge, tDVO)” to “Data Valid Out Time (after SCK edge, tDVO)” Added table: SPI Switching characteristics at 1.7V (1.7 - 3.6V) NOTE added to KM Signal Multiplexing and Pin Assignments topic
Rev3	04/2013	Updated orderable part numbers Updated Table: ESD handling ratings • Add new row: Electrostatic discharge voltage, charged-device mode Updated Table: Voltage and current operating behaviors Updated Table: Power consumption operating behaviors Updated "Inputs, tSUI" row in Table: SWD switching characteristics at 2.7 V (2.7 - 3.6 V) Updated "Inputs, tSUI" row in Table: AFE switching characteristics (1.7 V - 3.6 V) Updated "Supply voltage" minimum value in table: Voltage reference electrical specifications Added table: OD cells in SPI Switching specification Updated Table: VREF full-range operating behaviors Updated Table: ΣΔ ADC + PGA specifications Updated Table: ADC standalone specifications

Table continues on the next page...

Table 41. Revision History (continued)

Rev. No.	Date	Substantial Changes
Rev4	07/2013	Editorial changes through out the document. Values of table "Power mode transition operating behaviors" updated. In table "Power consumption operating behaviors": • Row I_{DD_RUN} value updated • Row I_{DD_WAIT} value updated • Row I_{DD_VLPR} value updated • Row I_{DD_VLPW} value updated • Row I_{DD_STOP} value updated • Row I_{DD_VLPS} value updated • Row I_{DD_VLLS3} value updated • Row I_{DD_VLLS2} value updated • Row I_{DD_VLLS1} value updated • Row I_{DD_VLLS0} value updated • Row I_{DD_VBAT} value updated • New row "I_{DD_VLLS0} with POR enabled" added. Values of table "General switching specifications" updated. In table "VREF full-range operating behaviors": • Row V_{tdrift}: value updated and footnote added. In table "LCD electricals": • Row I_{RBIAS}: values updated.
Rev5	10/2013	Table: Obtaining package dimensions updated
Rev6	11/2013	Updated Section Fields: • Row: Temperature range values updated. Updated Table: Power consumption operating behaviors

Rev7	1/2014	• Table: Power consumption operating behaviors
		  • All rows with temperature 110 °C updated to 105 °C
		  • Footnote 9 updated: An external power switch for VBAT should be present on board to have better battery life and keep VBAT pin powered in all conditions. There is no internal power switch in RTC.
		  • Row I_{DD_VLPR}: Minimum value updated
		  • Row I_{DD_VLLS1}: Typ value updated
		  • Row I_{DD_VLLS0} with POR circuit disabled: Typ value updated
		  • Row I_{DD_VLLS0} with POR circuit enabled: Typ value updated
		• Table: EMC radiated emissions operating behaviors
		  • All TBD updated
		  • Footnote 2: f_{osc} value updated to 10 MHz
		• Table: ADC + PGA specifications
		  • Row CMMR: V_{id} value updated
		• Table: ADC standalone specifications
		  • Row CMMR: V_{id} value updated